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# Onsemi

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# 16 kb CMOS Parallel **EEPROM**

#### Description

The CAT28C17A is a fast, low power, 5 V-only CMOS Parallel EEPROM organized as 2K x 8-bits. It requires a simple interface for in-system programming. On-chip address and data latches, self-timed write cycle with auto-clear and V<sub>CC</sub> power up/down write protection eliminate additional timing and protection hardware. DATA Polling and a RDY/ $\overline{BSY}$  pin signal the start and end of the self-timed write cycle. Additionally, the CAT28C17A features hardware write protection.

The CAT28C17A is manufactured using ON Semiconductor's advanced CMOS floating gate technology. It is designed to endure 10,000 program/erase cycles and has a data retention of 10 years. The device is available in JEDEC approved 28-pin DIP and SOIC or 32-pin PLCC packages.

#### Features

- Fast Read Access Times: 200 ns
- Low Power CMOS Dissipation:
  - Active: 25 mA Max.
  - Standby: 100 µA Max.
- Simple Write Operation:
  - On-chip Address and Data Latches
  - Self-timed Write Cycle with Auto-clear
- Fast Write Cycle Time: 10 ms Max
- End of Write Detection:
  - DATA Polling
  - RDY/BSY Pin
- Hardware Write Protection
- CMOS and TTL Compatible I/O
- 10,000 Program/Erase Cycles
- 10 Year Data Retention
- Commercial, Industrial and Automotive Temperature Ranges



## **ON Semiconductor®**

http://onsemi.com



SOIC-28 J, K, W, X SUFFIX CASE 751BM



#### N. G SUFFIX CASE 776AK

#### **PIN FUNCTION**

Pin Name	Function
A <sub>0</sub> -A <sub>10</sub>	Address Inputs
I/O <sub>0</sub> -I/O <sub>7</sub>	Data Inputs/Outputs
RDY/BUSY	Ready/BUSY Status
CE	Chip Enable
ŌE	Output Enable
WE	Write Enable
V <sub>CC</sub>	5 V Supply
V <sub>SS</sub>	Ground
NC	No Connect

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

#### **PIN CONFIGURATION**

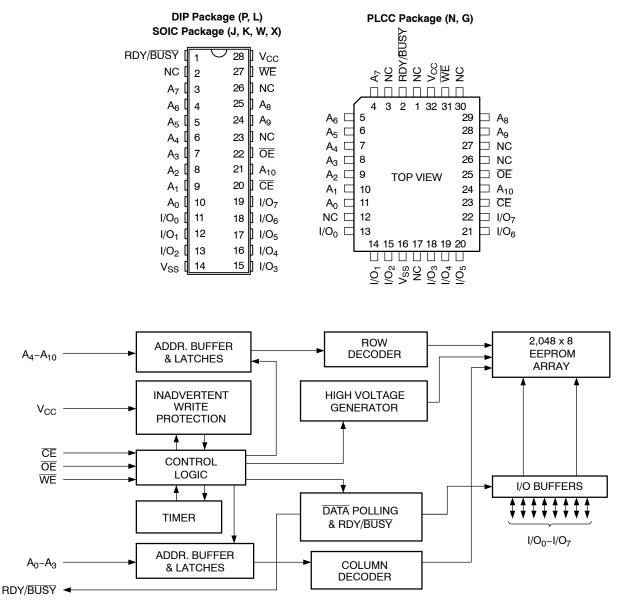


Figure 1. Block Diagram

#### Table 1. MODE SELECTION

Mode	CE	WE	ŌE	I/O	Power
Read	L	Н	L	D <sub>OUT</sub>	ACTIVE
Byte Write (WE Controlled)	L		Н	D <sub>IN</sub>	ACTIVE
Byte Write (CE Controlled)		L	Н	D <sub>IN</sub>	ACTIVE
Standby and Write Inhibit	Н	Х	Х	High-Z	STANDBY
Read and Write Inhibit	Х	н	Н	High-Z	ACTIVE

#### Table 2. CAPACITANCE (T<sub>A</sub> = 25°C, f = 1.0 MHz, V<sub>CC</sub> = 5 V)

Symbol	Test	Мах	Conditions	Units
C <sub>I/O</sub> (Note 1)	Input/Output Capacitance	10	$V_{I/O} = 0 V$	pF
C <sub>IN</sub> (Note 1)	Input Capacitance	6	V <sub>IN</sub> = 0 V	pF

1. This parameter is tested initially and after a design or process change that affects the parameter.

#### Table 3. ABSOLUTE MAXIMUM RATINGS

Parameters	Ratings	Units
Temperature Under Bias	-55 to +125	°C
Storage Temperature	-65 to +150	°C
Voltage on Any Pin with Respect to Ground (Note 2)	-2.0 V to +V <sub>CC</sub> + 2.0 V	V
V <sub>CC</sub> with Respect to Ground	-2.0 to +7.0	V
Package Power Dissipation Capability (T <sub>A</sub> = 25°C)	1.0	W
Lead Soldering Temperature (10 secs)	300	°C
Output Short Circuit Current (Note 3)	100	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

The minimum DC input voltage is -0.5 V. During transitions, inputs may undershoot to -2.0 V for periods of less than 20 ns. Maximum DC voltage on output pins is V<sub>CC</sub> + 0.5 V, which may overshoot to V<sub>CC</sub> + 2.0 V for periods of less than 20 ns.

3. Output shorted for no more than one second. No more than one output shorted at a time.

#### Table 4. RELIABILITY CHARACTERISTICS (Note 4)

Symbol	Parameter	Test Method	Min	Max	Units
N <sub>END</sub>	Endurance	MIL-STD-883, Test Method 1033	10,000		Cycles/Byte
T <sub>DR</sub>	Data Retention	MIL-STD-883, Test Method 1008	10		Years
V <sub>ZAP</sub>	ESD Susceptibility	MIL-STD-883, Test Method 3015	2,000		V
I <sub>LTH</sub> (Note 5)	Latch-Up	JEDEC Standard 17	100		mA

4. This parameter is tested initially and after a design or process change that affects the parameter.

5. Latch-up protection is provided for stresses up to 100 mA on address and data pins from -1 V to  $V_{CC}$  + 1 V.

## Table 5. D.C. OPERATING CHARACTERISTICS (V\_{CC} = 5 V $\pm 10\%$ , unless otherwise specified.)

			Limits			
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
ICC	V <sub>CC</sub> Current (Operating, TTL)	$\overline{CE} = \overline{OE} = V_{IL},$ f = 1/t <sub>RC</sub> min, All I/O's Open			35	mA
I <sub>CCC</sub> (Note 6)	V <sub>CC</sub> Current (Operating, CMOS)	$\overline{CE} = \overline{OE} = V_{ILC},$ f = 1/t <sub>RC</sub> min, All I/O's Open			25	mA
I <sub>SB</sub>	V <sub>CC</sub> Current (Standby, TTL)	CE = V <sub>IH</sub> , All I/O's Open			1	mA
I <sub>SBC</sub> (Note 7)	V <sub>CC</sub> Current (Standby, CMOS)	CE = V <sub>IHC</sub> , All I/O's Open			100	μΑ
ILI	Input Leakage Current	$V_{IN} = GND$ to $V_{CC}$	-10		10	μΑ
Ι <sub>LO</sub>	Output Leakage Current	$\frac{V_{OUT}}{CE} = GND \text{ to } V_{CC},$ $\overline{CE} = V_{IH}$	-10		10	μΑ
V <sub>IH</sub> (Note 7)	High Level Input Voltage		2		V <sub>CC</sub> + 0.3	V
V <sub>IL</sub> (Note 6)	Low Level Input Voltage		-0.3		0.8	V
V <sub>OH</sub>	High Level Output Voltage	I <sub>OH</sub> = -400 μA	2.4			V
V <sub>OL</sub>	Low Level Output Voltage	I <sub>OL</sub> = 2.1 mA			0.4	V
V <sub>WI</sub>	Write Inhibit Voltage		3.0			V

# Table 6. A.C. CHARACTERISTICS, READ CYCLE (V<sub>CC</sub> = 5 V $\pm$ 10%, unless otherwise specified.)

		28C17A-20		
Symbol	Parameter	Min	Max	Units
t <sub>RC</sub>	Read Cycle Time	200		ns
t <sub>CE</sub>	CE Access Time		200	ns
t <sub>AA</sub>	Address Access Time		200	ns
t <sub>OE</sub>	OE Access Time		80	ns
t <sub>LZ</sub> (Note 8)	CE Low to Active Output	0		ns
t <sub>OLZ</sub> (Note 8)	OE Low to Active Output	0		ns
t <sub>HZ</sub> (Notes 8, 9)	CE High to High-Z Output		55	ns
t <sub>OHZ</sub> (Notes 8, 9)	OE High to High-Z Output		55	ns
t <sub>OH</sub> (Note 8)	Output Hold from Address Change	0		ns

8. This parameter is tested initially and after a design or process change that affects the parameter.

9. Output floating (High-Z) is defined as the state when the external data line is no longer driven by the output buffer.

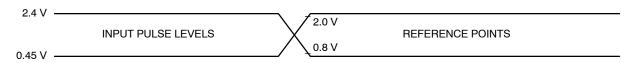
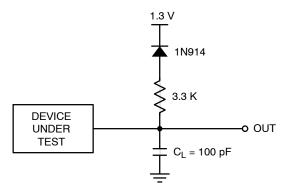


Figure 2. A.C. Testing Input/Output Waveform (Note 10)

10. Input rise and fall times (10% and 90%) < 10 ns.



C<sub>L</sub> INCLUDES JIG CAPACITANCE

Figure 3. A.C. Testing Load Circuit (example)

Table 7. A.C. CHARACTERISTICS, WRITE CYCLE ( $V_{CC}$ = 5 V ±10%, unless otherwise specified.)
--

		28C17A-20		
Symbol	Parameter	Min	Max	Units
t <sub>WC</sub>	Write Cycle Time		10	ms
t <sub>AS</sub>	Address Setup Time	10		ns
t <sub>AH</sub>	Address Hold Time	100		ns
t <sub>CS</sub>	CE Setup Time	0		ns
t <sub>CH</sub>	CE Hold Time	0		ns
t <sub>CW</sub> (Note 11)	CE Pulse Time	150		ns
t <sub>OES</sub>	OE Setup Time	15		ns
t <sub>OEH</sub>	OE Hold Time	15		ns
t <sub>WP</sub> (Note 11)	WE Pulse Width	150		ns
t <sub>DS</sub>	Data Setup Time	50		ns
t <sub>DH</sub>	Data Hold Time	10		ns
t <sub>DL</sub>	Data Latch Time	50		ns
t <sub>INIT</sub> (Note 12)	Write Inhibit Period After Power–up	5	20	ms
t <sub>DB</sub>	Time to Device Busy		80	ns

11. A write pulse of less than 20 ns duration will not initiate a write cycle.

12. This parameter is tested initially and after a design or process change that affects the parameter.

# DEVICE OPERATION

## Read

Data stored in the CAT28C17A is transferred to the data bus when  $\overline{WE}$  is held high, and both  $\overline{OE}$  and  $\overline{CE}$  are held low. The data bus is set to a high impedance state when either  $\overline{CE}$ or  $\overline{OE}$  goes high. This 2–line control architecture can be used to eliminate bus contention in a system environment.

#### Ready/BUSY (RDY/BUSY)

The RDY/ $\overline{\text{BUSY}}$  pin is an open drain output which indicates device status during programming. It is pulled low during the write cycle and released at the end of programming. Several devices may be OR-tied to the same RDY/ $\overline{\text{BUSY}}$  line.

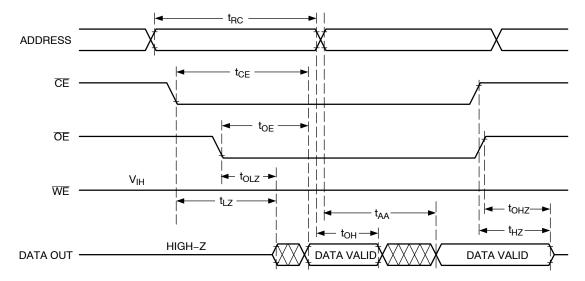
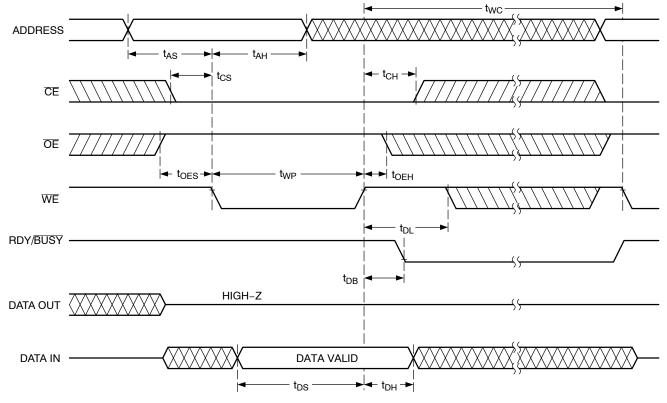


Figure 4. Read Cycle





#### **Byte Write**

A write cycle is executed when both  $\overline{CE}$  and  $\overline{WE}$  are low, and  $\overline{OE}$  is high. Write cycles can be initiated using either  $\overline{WE}$ or  $\overline{CE}$ , with the address input being latched on the falling edge of  $\overline{WE}$  or  $\overline{CE}$ , whichever occurs last. Data, conversely, is latched on the rising edge of  $\overline{WE}$  or  $\overline{CE}$ , whichever occurs first. Once initiated, a byte write cycle automatically erases the addressed byte and the new data is written within 10 ms.

#### **DATA** Polling

DATA polling is provided to indicate the completion of a byte write cycle. Once a byte write cycle is initiated, attempting to read the last byte written will output the complement of that data on  $I/O_7$  ( $I/O_0$ – $I/O_6$  are indeterminate) until the programming cycle is complete. Upon completion of the self-timed byte write cycle, all I/O's will output true data during a read cycle.

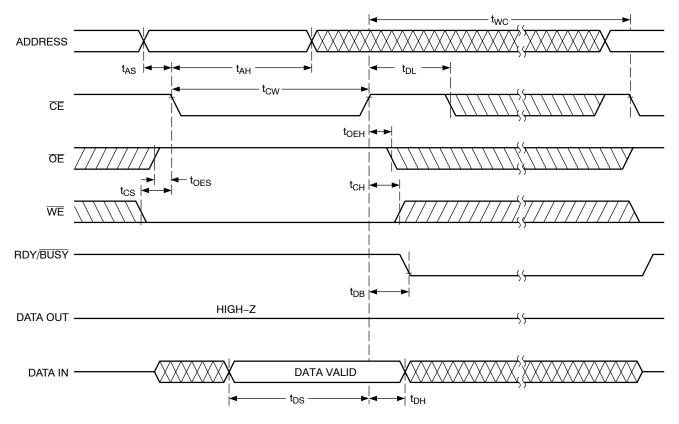


Figure 6. Byte Write Cycle [CE Controlled]

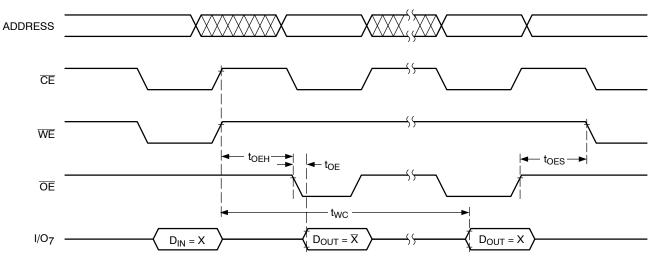


Figure 7. DATA Polling

#### Hardware Data Protection

The following is a list of hardware data protection features that are incorporated into the CAT28C17A.

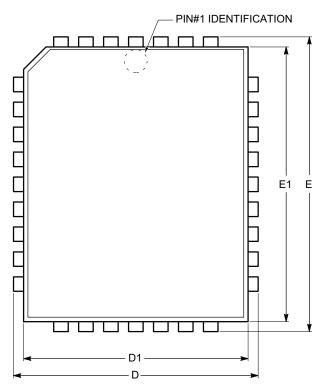
- 1.  $V_{CC}$  sense provides for write protection when  $V_{CC}$  falls below 3.0 V min.
- 2. A power on delay mechanism, t<sub>INIT</sub> (see AC characteristics), provides a 5 to 20 ms delay before

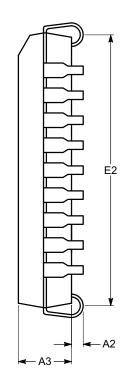
a write sequence, after  $V_{CC}$  has reached 3.0 V min.

- 3. Write inhibit is activated by holding any one of  $\overline{OE}$  low,  $\overline{CE}$  high or  $\overline{WE}$  high.
- 4. Noise pulses of less than 20 ns on the  $\overline{WE}$  or  $\overline{CE}$  inputs will not result in a write cycle.

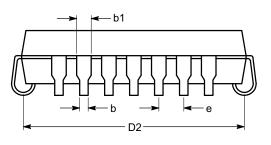
#### **PACKAGE DIMENSIONS**

PLCC 32 CASE 776AK-01 ISSUE O





END VIEW



TOP VIEW

SIDE VIEW

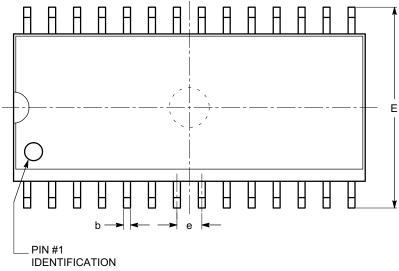
#### Notes:

All dimensions are in millimeters.
Complies with JEDEC MS-016.

SYMBOL	MIN	NOM	МАХ
A2	0.38		
A3	2.54		2.80
b	0.33		0.54
b1	0.66		0.82
D	12.32		12.57
D1	11.36		11.50
D2	9.56		11.32
Е	14.86		15.11
E1	13.90		14.04
E2	12.10		13.86
е		1.27 BSC	

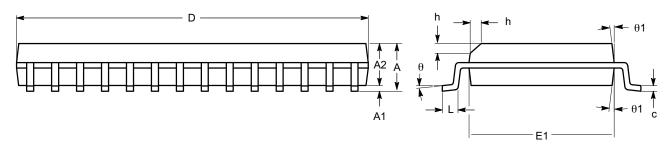
## **PACKAGE DIMENSIONS**

SOIC-28, 300 mils CASE 751BM-01 ISSUE O



TOP VIEW

SYMBOL	MIN	NOM	MAX
А	2.35		2.65
A1	0.10		0.30
A2	2.05		2.55
b	0.31		0.51
с	0.20		0.33
D	17.78		18.03
E	10.11		10.51
E1	7.34		7.60
е		1.27 BSC	
h	0.25		0.75
L	0.40		1.27
θ	0°		8°
θ1	5°		15°



SIDE VIEW

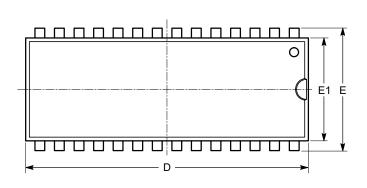
END VIEW

#### Notes:

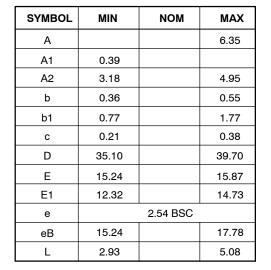
All dimensions are in millimeters. Angles in degrees.
Complies with JEDEC MS-013.

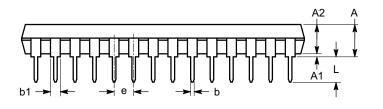
## **PACKAGE DIMENSIONS**

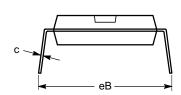
PDIP-28, 600 mils CASE 646AE-01 **ISSUE A** 



TOP VIEW







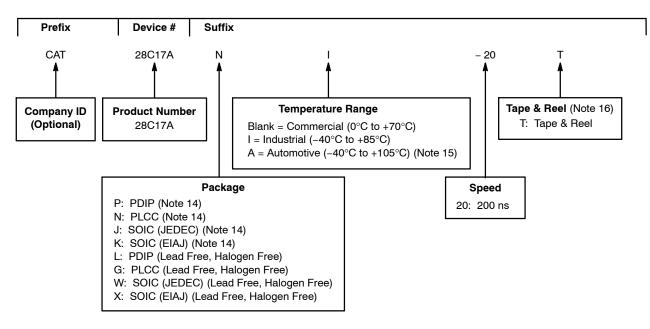
END VIEW

SIDE VIEW

Notes:

All dimensions are in millimeters.
Complies with JEDEC MS-011.

#### **Example of Ordering Information**



13. The device used in the above example is a CAT28C17ANI-20T (PLCC, Industrial Temperature, 200 ns Access Time, Tape & Reel). 14. Solder-plate (tin-lead) packages, contact Factory for availability.

15.-40°C to +125°C is available upon request.

16. For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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